Number 7 104 organic adj2 switch\$3 USPAT; US-PGPU	2004/09/15
05 FGF(	
EPO; JI	· 1
DERWEN	· •
IBM TDE	1
9 17 (organic adj2 switch\$3) and (first adj3 USPAT;	2004/09/15
electrode) US-PGPU	I ' '
EPO; JE	· •
DERWENT	
IBM TDE	I
10 15 ((organic adj2 switch\$3) and (first adj3   USPAT;	2004/09/15
electrode)) and (second adj3 electrode) US-PGPU	JB;   14:14
EPO; JI	°O;
DERWENT	
IBM_TDF	
11 219 (first adj3 electrode) same organic same USPAT;	2004/09/15
diod\$2 US-PGPU	· •
EPO; JI	· •
DERWENT	-
IBM_TDF	
10 ((first adj3 electrode) same organic same USPAT;	2004/09/15
diod\$2) same (second adj3 electrode) same US-PGPU	- 1
memory EPO; JI	
DERWENT IBM TDI	
8 7 (organic adj2 switch\$3) same (first adj3 USPAT;	2004/09/15
electrode) US-PGPU	1
EPO; JE	
DERWEN	
IBM TDE	*
14 2 ("6055180").PN. USPĀT;	2004/09/15
US-PGPU	,
EPO; JI	0;
DERWENT	1;
IBM_TDI	
13	2004/09/15
US-PGPU	· .
EPO; JI	
DERWENT	· ·
IBM_TDF	
15 23 tanabe-takahisa.in. USPĀT; US-PGPU	2004/09/15 JB: 14:23
US-PGPC EPO; JI	· 1
DERWENT	. 1
IBM TDE	
16 0 tanabe-takahisa-\$.in. USPAT;	2004/09/15
US-PGPU	I
EPO; JI	· •
DERWENT	
IBM_TDF	3
- 10 organic adj3 switch\$3 adj3 memory USPAT;	2004/09/15
US-PGPU	
EPO; JI	
DERWENT	
IBM_TDF	
- 115 organic same (switch\$3 adj2 memory) USPAT;	2004/09/15
US-PGPU	
EPO; JI	1
DERWENT IBM TDE	
- 5 (organic same (switch\$3 adj2 memory)) USPAT;	2004/09/15
same (first adj2 electrode) US-PGPU	
EPO; JE	
DERWENT	I
IBM TDE	

-	16	1 '	USPAT;	2004/09/15
		adj3 memory)	US-PGPUB;	12:01
			EPO; JPO;	
İ			DERWENT;	
		/	IBM_TDB	2004/00/15
-	11		USPAT;	2004/09/15
1		((first adj2 electrod\$2) same (organic	US-PGPUB;	12:01
		adj3 memory))	EPO; JPO;	
			DERWENT;	
1		/64	IBM_TDB	2004/00/15
-	39		USPAT;	2004/09/15
		memory) and (second electrod\$2)	US-PGPUB;	12:01
			EPO; JPO;	
			DERWENT;	
l _	22	(/first adia alastmadea) and (amounts	IBM_TDB USPAT;	2004/09/15
-	22	((first adj2 electrod\$2) and (organic adj3 memory) and (second electrod\$2)) and	· ·	12:02
			US-PGPUB;	12:02
		diode	EPO; JPO;	
			DERWENT;	
l _	11	///finat adi2 alastmade2\ /	IBM_TDB	2004/00/15
-	11		USPAT;	2004/09/15
		adj3 memory) and (second electrod\$2)) and	US-PGPUB;	12:07
ĺ		diode) and (organic same (switch\$3 adj2	EPO; JPO;	
		memory))	DERWENT;	
	10	/diada adi2 lawan) name /amand adi2	IBM_TDB	2004/00/15
-	19	1, 3, 4, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1,	USPAT; US-PGPUB;	2004/09/15
1		electrode)	f .	12:07
1		·	EPO; JPO;	
			DERWENT;	
	16	//4: -44:2 1> /4 -4:2	IBM_TDB	2004/00/15
-	15		USPAT;	2004/09/15
		electrode)) near5 (first adj2 electrode)	US-PGPUB;	12:07
			EPO; JPO;	
1			DERWENT;	
l _	-	////diodo adia layan\ noant /cocond cdia	IBM_TDB	2004/09/15
-	7		USPAT;	12:10
		electrode)) near5 (first adj2 electrode))	US-PGPUB;	12:10
		near10 organic) and (memory or semiconductor)	EPO; JPO; DERWENT;	
		Semi-conductor)	IBM TDB	
l _	14	(((diode adj2 layer) near5 (second adj2	USPAT;	2004/09/15
ł	14	electrode)) near5 (first adj2 electrode))	US-PGPUB;	12:09
		near10 organic	EPO; JPO;	12.00
			DERWENT;	
			IBM TDB	
_	n	(low adj2 electrode) same (up adj2	USPAT;	2004/09/15
		electrode) same diode same resistor	US-PGPUB;	12:11
		Jerose de la constante de la c	EPO; JPO;	~~
			DERWENT;	
			IBM TDB	
_	n	(low adj2 electrode) same (up adj2	USPAT;	2004/09/15
	ı	electrode) same diode	US-PGPUB;	12:12
[		Section of Samo around	EPO; JPO;	12.12
			DERWENT;	
			IBM TDB	
_	3784	((low or lower or first) adj2 electrode)	USPAT;	2004/09/15
		same ((up or upper or high or second)	US-PGPUB;	12:13
		adj2 electrode) same diode	EPO; JPO;	
		J,	DERWENT;	
			IBM TDB	
_	141	(((low or lower or first) adj2 electrode)	USPAT;	2004/09/15
		same ((up or upper or high or second)	US-PGPUB;	12:17
		adj2 electrode) same diode) same memory	EPO; JPO;	
		, in the second	DERWENT;	
			IBM TDB	
_	5	((((low or lower or first) adj2	USPAT;	2004/09/15
		electrode) same ((up or upper or high or	US-PGPUB;	12:16
		second) adj2 electrode) same diode) same	EPO; JPO;	
		memory) same (organic adj2 memory)	DERWENT;	
			IBM TDB	

-	4	((((low or lower or first) adj2	USPAT;	2004/09/15
		electrode) same ((up or upper or high or	US-PGPUB;	12:17
	į į	second) adj2 electrode) same diode) same	EPO; JPO;	
		memory) same (organic adj2 layer)	DERWENT;	ļ
			IBM_TDB	
-	36	((((low or lower or first) adj2	USPAT;	2004/09/15
		electrode) same ((up or upper or high or	US-PGPUB;	13:53
		second) adj2 electrode) same diode) same	EPO; JPO;	
		memory) and 365/\$7.ccls.	DERWENT;	
		-	IBM_TDB	